

## K. Memory (Design & Process Technology) 분과

Room B

창의관 (110)

일 시 : 2월 17일(금) 11:20-12:35

세션명 : [FB2-K] Phase Change Memories

좌 장 : 조성익(전북대학교)

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FB2-K-1 11:20-11:50 **[Invited]** Critical Consideration and Requirements of Access Device for Scalable Phase Change Memory

저자: 박해찬, 박남균, 김석기, 김명섭, 이세호, 최강식, 이정훈, 홍성주

소속: 하이닉스반도체 선행소자A팀

FB2-K-2 11:50-12:05 PCRAM Flip-flop Circuit with Sequential Sleep-in Control Scheme

저자: Jun-Myung Choi, Chul-Moon Jung, and Kyeong-Sik Min

소속: School of Electrical Engineering, Kookmin University

FB2-K-3 12:05-12:20 The Effect of Carbon Incorporated into  $\text{In}_3\text{Sb}_1\text{Te}_2$  on Phase Change Characteristics in Phase Change Memory

저자: 김현수<sup>1,4</sup>, 김용태<sup>2</sup>, 김용인<sup>3</sup>, 성만영<sup>4</sup>

소속: <sup>1</sup>삼성전자 Memory 사업부, <sup>2</sup>한국과학기술연구원, <sup>3</sup>KAIST, <sup>4</sup>고려대학교

FB2-K-4 12:20-12:35 Improved Switching Uniformity in  $\text{Ge}_2\text{Sb}_2\text{Te}_5$  based Resistive Switching Memory Device by using Internal Resistor

저자: Jiyong Woo<sup>1</sup>, Seungjae Jung<sup>1</sup>, Jubong Park<sup>1</sup>, Seonghyun Kim<sup>1</sup>, Wootae Lee<sup>1</sup>, Dasesoek Lee<sup>1</sup>, Euijun Cha<sup>2</sup>, and Hyunsang Hwang<sup>1,2</sup>

소속: <sup>1</sup>School of Materials Science and Engineering, Gwangju Institute of Science and Technology, <sup>2</sup>Department of Nanobio Materials and Electronics, Gwangju Institute of Science and Technology, Gwangju Institute of Science and Technology